What is claimed is:

1. A Group III nitride semiconductor light-emitting element including an n-type contact layer of n-type GaN, an n-type clad layer of n-type $Al_xGa_{1-x-y}In_yN$ ($0<x<1$, $0\leq y<1$, $0<x+y<1$), an active layer, a p-type clad layer, and a p-type contact layer, comprising:

a crack-preventing layer of n-type GaN provided between the n-type contact layer and the n-type clad layer,

wherein the crack-preventing layer has a dopant concentration lower than that of the n-type contact layer.

2. The light-emitting element according to claim 1, wherein the crack-preventing layer has a dopant concentration lower than 4×10^{18} cm^{-3}.

3. The light-emitting element according to claim 2, wherein the crack-preventing layer has a dopant concentration within a range of 5×10^{16} cm^{-3} to 5×10^{17} cm^{-3}.

4. The light-emitting element according to claim 1, wherein the n-type contact layer has a dopant concentration within a range of 4×10^{18} cm^{-3} to 2×10^{19} cm^{-3}.

5. The light-emitting element according to claim 1, wherein a dopant of the crack-preventing layer is either one of Si and Ge.

6. The light-emitting element according to claim 1, wherein a dopant of the n-type contact layer is either one of Si and Ge.

7. A method of manufacturing a semiconductor light-emitting element having a multilayered structure

constituted by sequentially stacking layers of Group III nitride semiconductors one upon another on a substrate, the method comprising:

an n-type contact-layer forming step of forming an n-type contact layer of n-type GaN, and

a crack-preventing layer forming step of forming a crack-preventing layer of n-type GaN, the crack-preventing layer having a dopant concentration lower than that of the n-type contact layer.

8. The method according to claim 7, wherein the crack-preventing layer forming step includes a step of reducing an amount of supply of a dopant material used in the n-type contact-layer forming step.